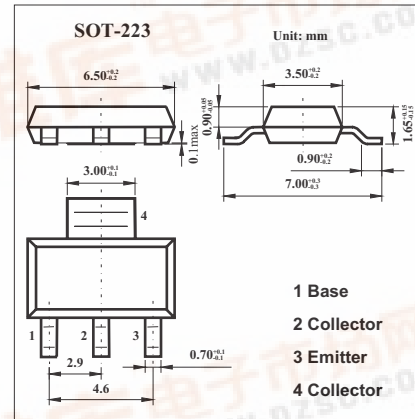


SMD Type Transistors

NPN Silicon Planar High Voltage Transistor
FZT658

■ Features

- 400 Volt V_{CEO}
- Low saturation voltage



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CBO}	400	V
Collector-Emitter Voltage	V _{CEO}	400	V
Emitter-Base Voltage	V _{EBO}	5	V
Peak Pulse Current	I _{CM}	1	A
Continuous Collector Current	I _C	0.5	A
Power Dissipation at T _{amb} =25°C	P _{tot}	2	W
Operating and Storage Temperature Range	T _j ; T _{stg}	-55 to +150	°C

FZT658

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ.	Max	Unit
Breakdown Voltage	V(BR)CBO	Ic=100μA	400			V
Breakdown Voltage	V(BR)CEO	Ic=10mA*	400			V
Breakdown Voltage	V(BR)EBO	Ie=100μA	5			V
Collector Cut-Off Current	IcBO	Vcb=320V			100	nA
Emitter Cut-Off Current	IeBO	VEB=4V			100	nA
Collector-Emitter Saturation Voltage	VCE(sat)	Ic=20mA, Ib=1mA*			0.3	V
		Ic=50mA, Ib=5mA*			0.25	V
		Ic=100mA, Ib=10mA			0.5	V
Base-Emitter Saturation Voltage	VBE(sat)	Ic=100mA, Ib=10mA*			0.9	V
Base-Emitter Turn-On Voltage	VBE(on)	Ic=100mA, VCE=5V*			1.0	V
Static Forward Current Transfer Ratio	hFE	Ic=1mA, VCE=5V*	50			
		Ic=100mA, VCE=5V*	50			
		Ic=200mA, VCE=10V*	40			
Transition Frequency	fT	Ic=10mA, VCE=20V, f=20MHz	50			MHz
Output Capacitance	Cobo	Vcb=20V, f=1MHz			10	pF
Switching Times	ton	Ic=100mA, Vcc=100V			130	ns
	toff	Ib1=10mA, Ib2=-20mA			3300	ns

* Measured under pulsed conditions. Pulse Width=300μs. Duty cycle≤2%

■ Marking

Marking	FZT658
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